

## General Description

FSMOS<sup>®</sup> MOSFET is based on Oriental Semiconductor's unique device design to achieve low  $R_{DS(on)}$ , low gate charge, fast switching and excellent avalanche characteristics. The high  $V_{th}$  series is specially designed to use in power supply systems with driving voltage of more than 10V.

## Features

- Low  $R_{DS(on)}$  & FOM (Figure of Merit)
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

## Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Inverters
- UPS



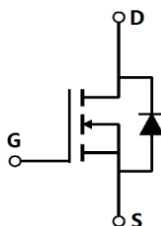
## Key Performance Parameters

| Parameter                         | Value | Unit       |
|-----------------------------------|-------|------------|
| $V_{DS}$                          | 80    | V          |
| $I_D$ , pulse                     | 256   | A          |
| $R_{DS(on)}$ , max @ $V_{GS}=10V$ | 8     | m $\Omega$ |
| $Q_g$                             | 22.4  | nC         |

## Marking Information

| Product Name | Package | Marking    |
|--------------|---------|------------|
| SFS08R08KNF  | TO263   | SFS08R08KN |

## Package & Pin information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

| Parameter                                                                 | Symbol                | Value      | Unit               |
|---------------------------------------------------------------------------|-----------------------|------------|--------------------|
| Drain-source voltage                                                      | $V_{DS}$              | 80         | V                  |
| Gate-source voltage                                                       | $V_{GS}$              | $\pm 20$   | V                  |
| Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$         | $I_D$                 | 64         | A                  |
| Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{D, \text{pulse}}$ | 256        | A                  |
| Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$ | $I_S$                 | 64         | A                  |
| Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{S, \text{pulse}}$ | 256        | A                  |
| Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$                | $P_D$                 | 87         | W                  |
| Single pulsed avalanche energy <sup>5)</sup>                              | $E_{AS}$              | 25         | mJ                 |
| Operation and storage temperature                                         | $T_{stg}, T_j$        | -55 to 175 | $^{\circ}\text{C}$ |

**Thermal Characteristics**

| Parameter                                          | Symbol          | Value | Unit                 |
|----------------------------------------------------|-----------------|-------|----------------------|
| Thermal resistance, junction-case                  | $R_{\theta JC}$ | 1.72  | $^{\circ}\text{C/W}$ |
| Thermal resistance, junction-ambient <sup>4)</sup> | $R_{\theta JA}$ | 62    | $^{\circ}\text{C/W}$ |

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

| Parameter                        | Symbol       | Min. | Typ. | Max. | Unit          | Test condition                                  |
|----------------------------------|--------------|------|------|------|---------------|-------------------------------------------------|
| Drain-source breakdown voltage   | $BV_{DSS}$   | 80   |      |      | V             | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$ |
| Gate threshold voltage           | $V_{GS(th)}$ | 2.0  |      | 4.0  | V             | $V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$     |
| Drain-source on-state resistance | $R_{DS(ON)}$ |      | 5.7  | 8    | m $\Omega$    | $V_{GS}=10\text{ V}, I_D=12\text{ A}$           |
| Gate-source leakage current      | $I_{GSS}$    |      |      | 100  | nA            | $V_{GS}=20\text{ V}$                            |
|                                  |              |      |      | -100 |               | $V_{GS}=-20\text{ V}$                           |
| Drain-source leakage current     | $I_{DSS}$    |      |      | 1    | $\mu\text{A}$ | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}$         |
| Gate resistance                  | $R_G$        |      | 3    |      | $\Omega$      | $f=1\text{ MHz}$ , Open drain                   |

### Dynamic Characteristics

| Parameter                    | Symbol       | Min. | Typ. | Max. | Unit | Test condition                                                                             |
|------------------------------|--------------|------|------|------|------|--------------------------------------------------------------------------------------------|
| Input capacitance            | $C_{iss}$    |      | 1722 |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=25\text{ V}$ ,<br>$f=100\text{ kHz}$                      |
| Output capacitance           | $C_{oss}$    |      | 693  |      | pF   |                                                                                            |
| Reverse transfer capacitance | $C_{rss}$    |      | 46.8 |      | pF   |                                                                                            |
| Turn-on delay time           | $t_{d(on)}$  |      | 22   |      | ns   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=40\text{ V}$ ,<br>$R_G=2\ \Omega$ ,<br>$I_D=40\text{ A}$ |
| Rise time                    | $t_r$        |      | 6    |      | ns   |                                                                                            |
| Turn-off delay time          | $t_{d(off)}$ |      | 33.4 |      | ns   |                                                                                            |
| Fall time                    | $t_f$        |      | 5.6  |      | ns   |                                                                                            |

### Gate Charge Characteristics

| Parameter            | Symbol        | Min. | Typ. | Max. | Unit | Test condition                                                        |
|----------------------|---------------|------|------|------|------|-----------------------------------------------------------------------|
| Total gate charge    | $Q_g$         |      | 22.4 |      | nC   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=40\text{ V}$ ,<br>$I_D=40\text{ A}$ |
| Gate-source charge   | $Q_{gs}$      |      | 7.1  |      | nC   |                                                                       |
| Gate-drain charge    | $Q_{gd}$      |      | 4.4  |      | nC   |                                                                       |
| Gate plateau voltage | $V_{plateau}$ |      | 5.1  |      | V    |                                                                       |

### Body Diode Characteristics

| Parameter                     | Symbol    | Min. | Typ. | Max. | Unit | Test condition                                                                 |
|-------------------------------|-----------|------|------|------|------|--------------------------------------------------------------------------------|
| Diode forward voltage         | $V_{SD}$  |      |      | 1.3  | V    | $I_S=12\text{ A}$ ,<br>$V_{GS}=0\text{ V}$                                     |
| Reverse recovery time         | $t_{rr}$  |      | 60   |      | ns   | $V_R=40\text{ V}$ ,<br>$I_S=40\text{ A}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge       | $Q_{rr}$  |      | 50.6 |      | nC   |                                                                                |
| Peak reverse recovery current | $I_{rrm}$ |      | 1.5  |      | A    |                                                                                |

### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=0.3\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

## Electrical Characteristics Diagrams

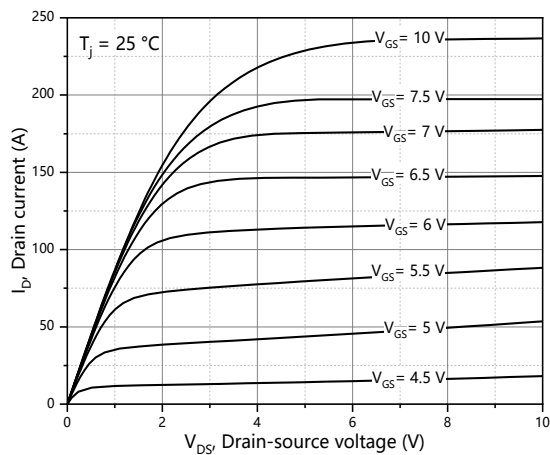


Figure 1. Typ. output characteristics

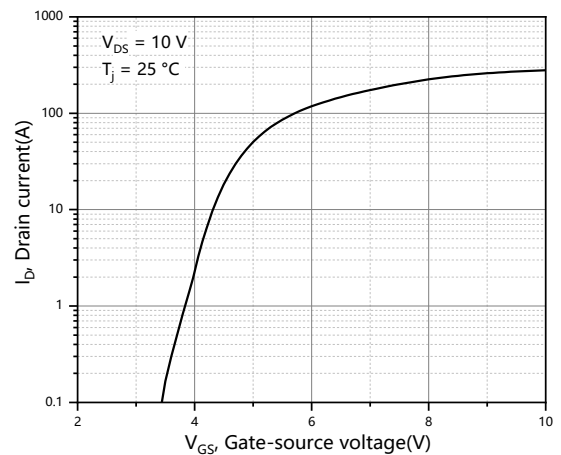


Figure 2. Typ. transfer characteristics

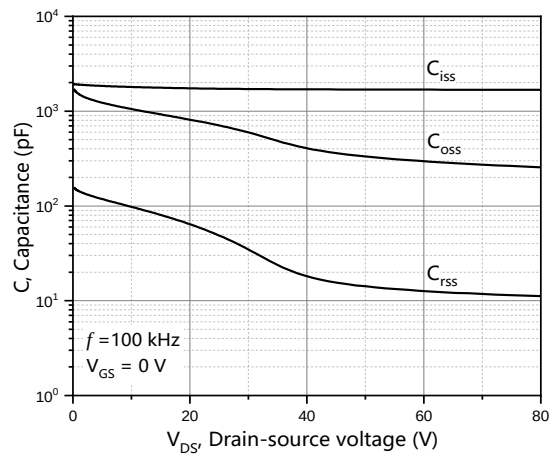


Figure 3. Typ. capacitances

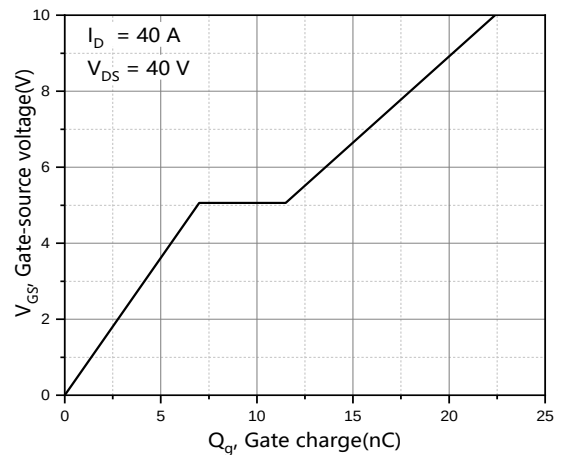


Figure 4. Typ. gate charge

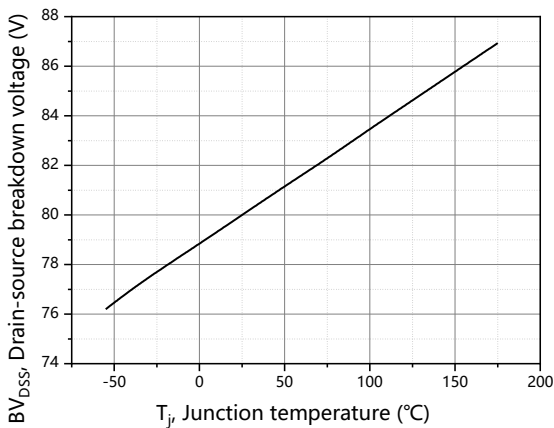


Figure 5. Drain-source breakdown voltage

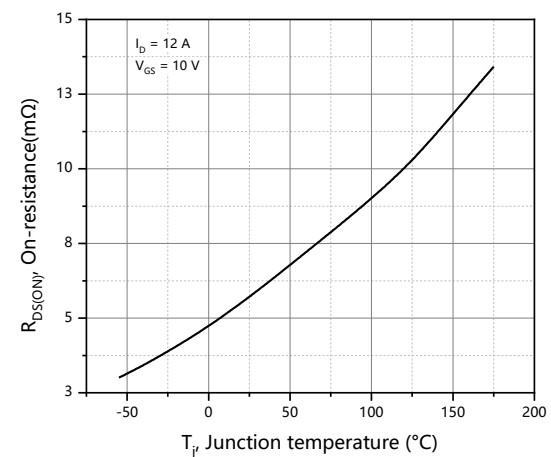
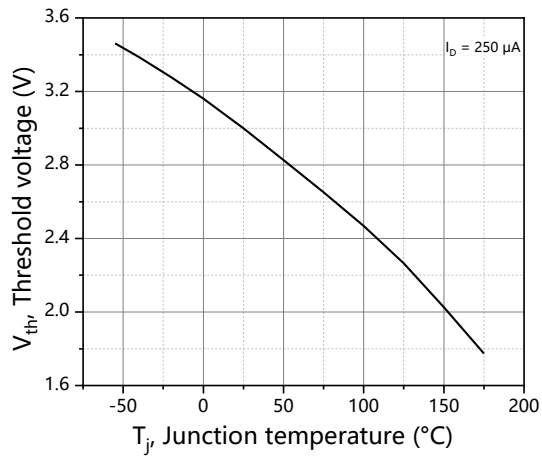
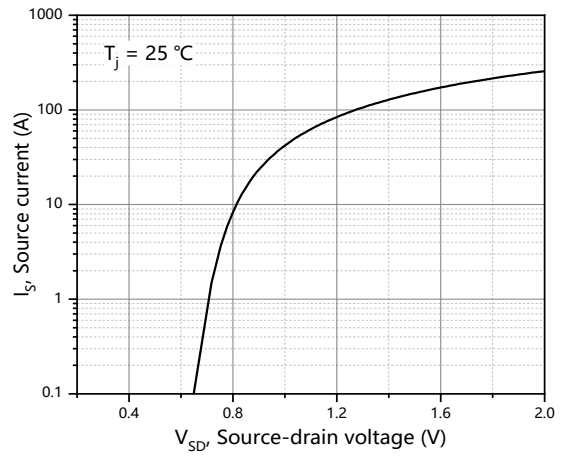


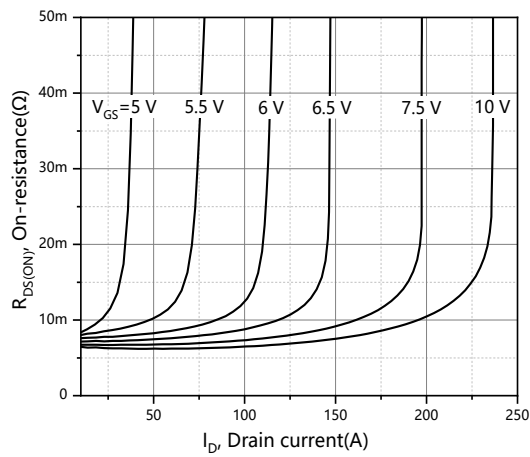
Figure 6. Drain-source on-state resistance



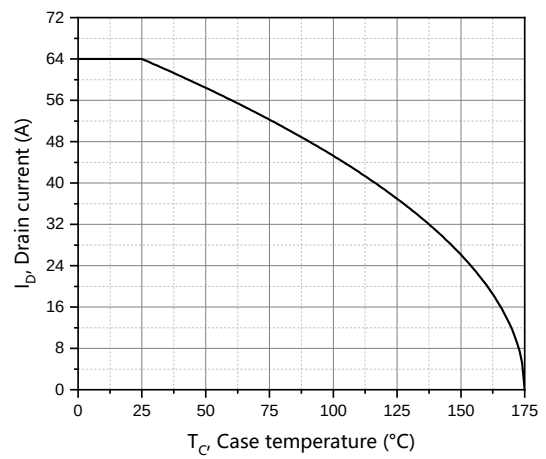
**Figure 7. Threshold voltage**



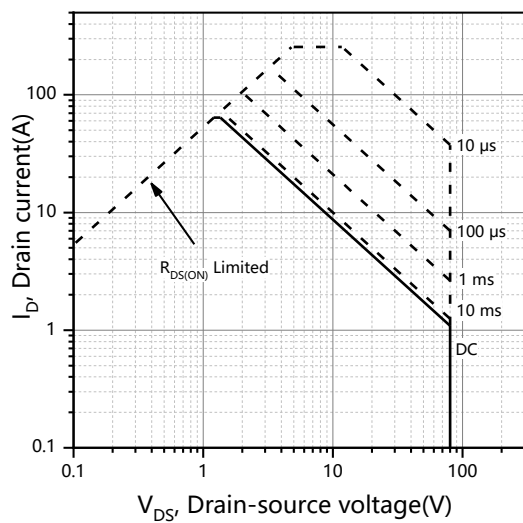
**Figure 8. Forward characteristic of body diode**



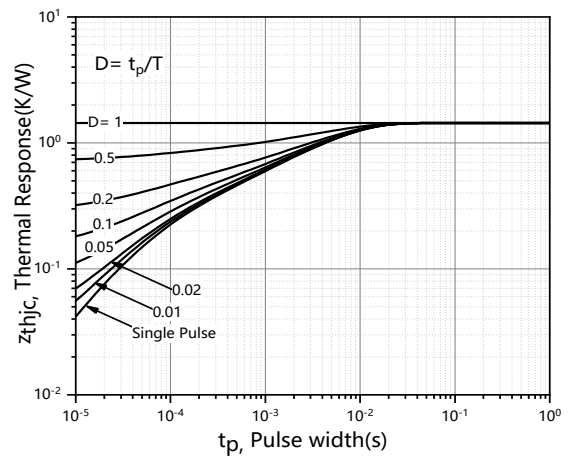
**Figure 9. Drain-source on-state resistance**



**Figure 10. Drain current**

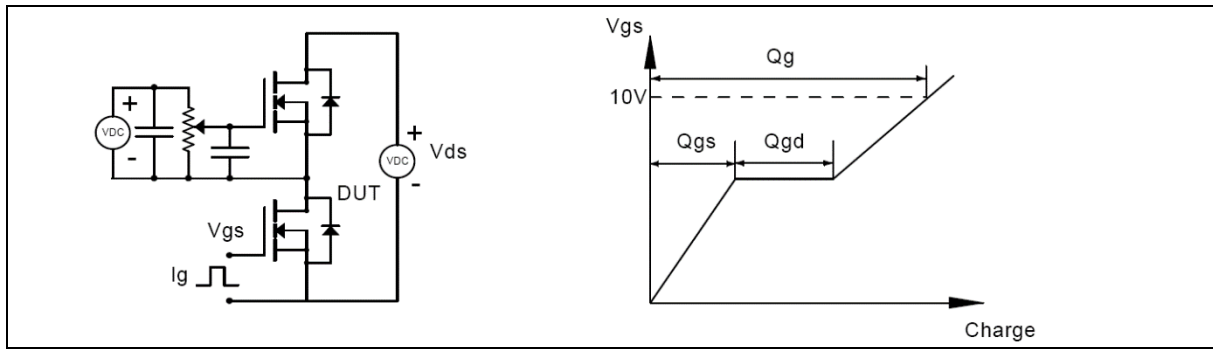


**Figure 11. Safe operation area Tc=25 °C**

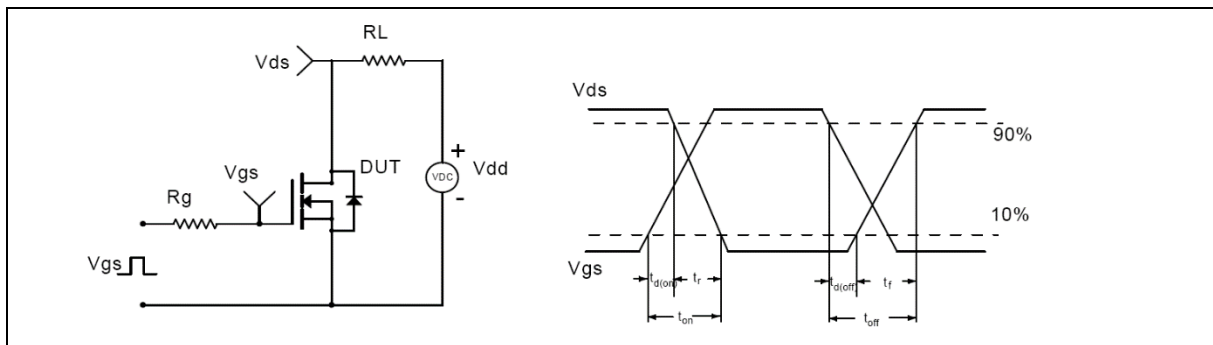


**Figure 12. Max. transient thermal impedance**

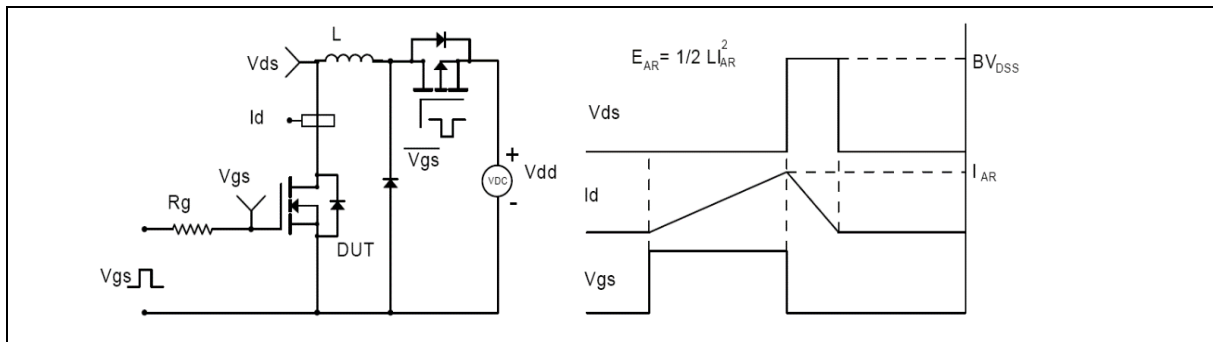
## Test circuits and waveforms



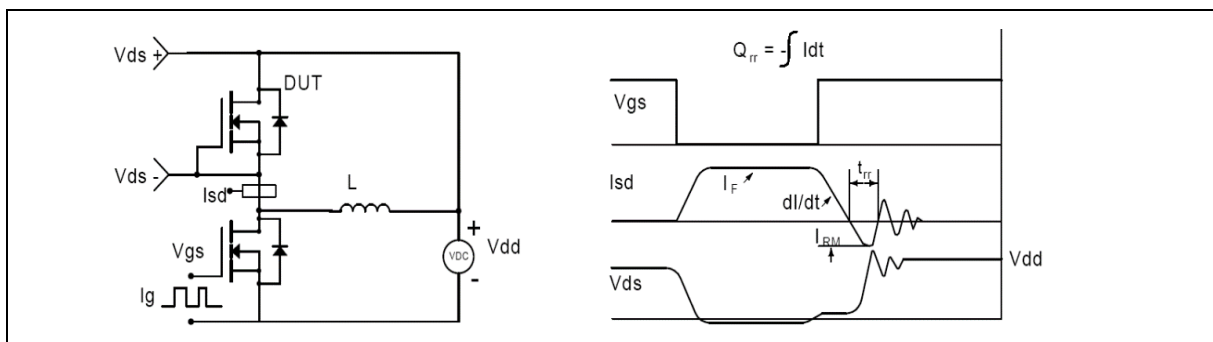
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

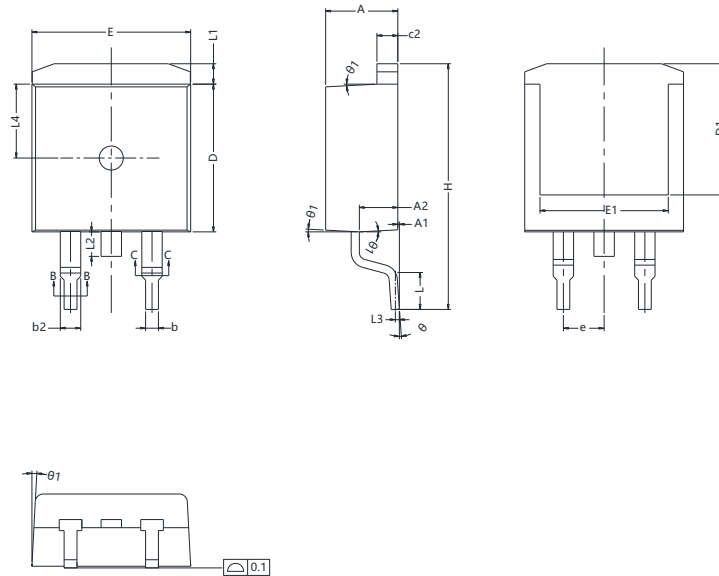


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information



| Symbol | mm       |       |       |
|--------|----------|-------|-------|
|        | Min      | Nom   | Max   |
| A      | 4.40     | 4.50  | 4.60  |
| A1     | 0.00     | 0.10  | 0.25  |
| A2     | 2.20     | 2.40  | 2.60  |
| b      | 0.76     | -     | 0.89  |
| b2     | 1.23     | -     | 1.37  |
| c      | 0.47     | -     | 0.60  |
| c1     | 0.46     | 0.51  | 0.56  |
| c2     | 1.25     | 1.30  | 1.35  |
| D      | 9.10     | 9.20  | 9.30  |
| D1     | 8.00     | -     | -     |
| E      | 9.80     | 9.90  | 10.00 |
| E1     | 7.80     | -     | -     |
| e      | 2.54BSC  |       |       |
| H      | 14.90    | 15.30 | 15.70 |
| L      | 2.00     | 2.30  | 2.30  |
| L1     | 1.17     | 1.27  | 1.40  |
| L2     | -        | -     | 1.75  |
| L3     | 0.25BSC  |       |       |
| L4     | 4.60 REF |       |       |
| θ      | 0°       | -     | 8°    |
| θ1     | 1°       | 3°    | 5°    |

Version 1: TO263-J package outline dimension

### Ordering Information

| Package Type | Units/ Reel | Reels/ Inner Box | Units/ Inner Box | Inner Box/ Carton Box | Units/ Carton Box |
|--------------|-------------|------------------|------------------|-----------------------|-------------------|
| TO263-J      | 800         | 1                | 800              | 10                    | 8000              |

### Product Information

| Product     | Package | Pb Free | RoHS | Halogen Free |
|-------------|---------|---------|------|--------------|
| SFS08R08KNF | TO263   | yes     | yes  | yes          |

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